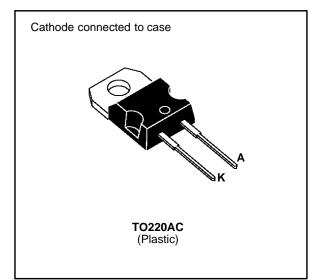


# **BYT 12P-1000**

# FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



# SUITABLE APPLICATIONS

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

# **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
Vrrm	Repetitive Peak Reverse Voltage	1000	V	
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage		1000	V
I <sub>FRM</sub>	Repetitive Peak Forward Current	t <sub>p</sub> ≤ 10μs	150	А
I <sub>F (RMS)</sub>	RMS Forward Current			А
I <sub>F (AV)</sub>	Average Forward Current	$\begin{array}{l} T_{case} = 100^{\circ}C\\ \delta = 0.5 \end{array}$	12	A
I <sub>FSM</sub>	Surge Non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	75	A
Р	Power Dissipation	$T_{case} = 100^{\circ}C$	25	W
T <sub>stg</sub> Tj	Storage and Junction Temperature Range	age and Junction Temperature Range		

# THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R <sub>th (j - c)</sub>	Junction-case	2	°C/W

# **ELECTRICAL CHARACTERISTICS**

# STATIC CHARACTERISTICS

Synbol	Test Conditions			Тур.	Max.	Unit
I <sub>R</sub>	T <sub>j</sub> = 25°C	$V_R = V_{RRM}$			50	μA
	T <sub>j</sub> = 100°C				2.5	mA
VF	T <sub>j</sub> = 25°C	I <sub>F</sub> = 12A			1.9	V
	T <sub>j</sub> = 100°C				1.8	

#### **RECOVERY CHARACTERISTICS**

Symbol		Test Conditions				Тур.	Max.	Unit
t <sub>rr</sub>	$T_j = 25^{\circ}C$	I <sub>F</sub> = 1A	di <sub>F</sub> /dt = - 15A/µs	$V_R = 30V$			155	ns
		I <sub>F</sub> = 0.5A	I <sub>R</sub> = 1A	$I_{rr} = 0.25A$			65	

#### TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions		Min.	Тур.	Max.	Unit
t <sub>IRM</sub>	di <sub>F</sub> /dt = - 50A/µs	$V_{CC} = 200 V I_F = 12A$			200	ns
	diғ/dt = - 100A/µs	L <sub>p</sub> ≤ 0.05μH    T <sub>j</sub> = 100°C See figure 11		120		
I <sub>RM</sub>	di <sub>F</sub> /dt = -50A/µs				7.8	А
	di⊧/dt = - 100A/µs			9		

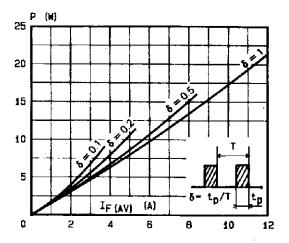
#### TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Conditions				Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	T <sub>j</sub> = 100°C di <sub>F</sub> /dt = - 12A/μs	$V_{CC} = 200V$ $L_p = 12\mu H$	$I_F = I_F (AV)$ See figure 12			4.5	

To evaluate the conduction losses use the following equations:

 $V_F = 1.47 + 0.026 I_F \qquad \qquad P = 1.47 \ x \ IF_{(AV)} + 0.026 \ I_F^{2}_{(RMS)}$ 

Figure 1. Low frequency power losses versus average current



### Figure 2. Peak current versus form factor

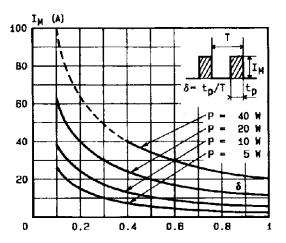




Figure 3. Non repetitive peak surge current versus overload duration

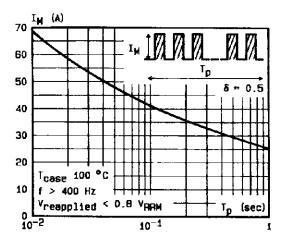


Figure 5. Voltage drop versus forward current

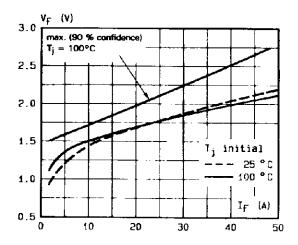


Figure 7. Recovery time versus di<sub>F</sub>/dt-

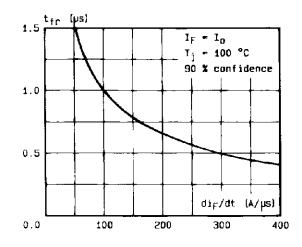


Figure 4. Thermal impedance versus pulse width

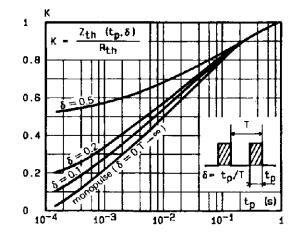


Figure 6. Recovery charge versus di<sub>F</sub>/dt

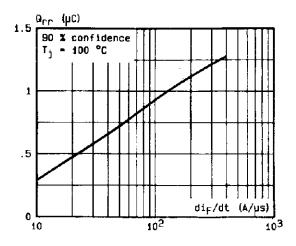
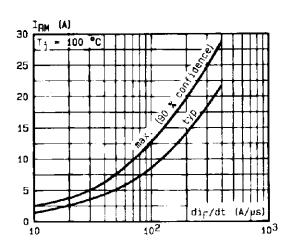


Figure 8. Peak reverse current versus diF/dt-



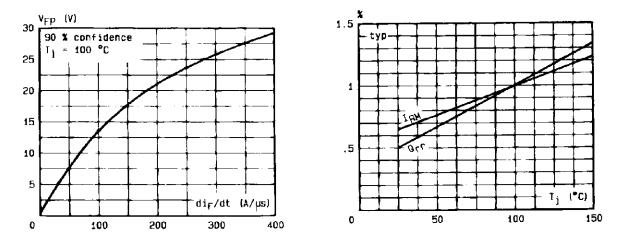


Figure 9. Peak forward voltage versus diF/dtt

Figure 10. Dynamic parameters versus junction temperature.

# Figure 11. Turn-off switching characteristics (without series inductance).

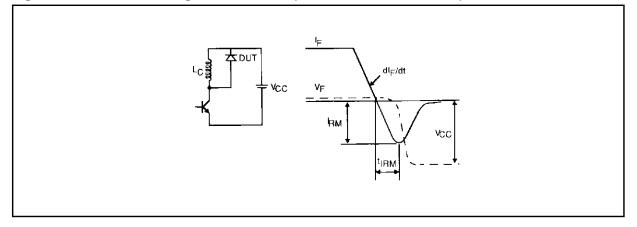
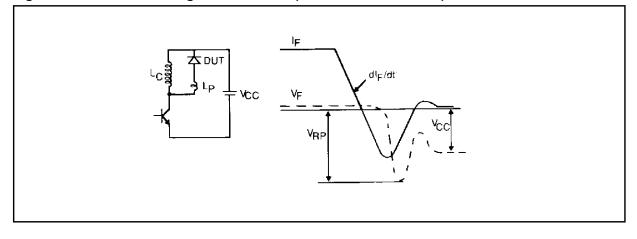


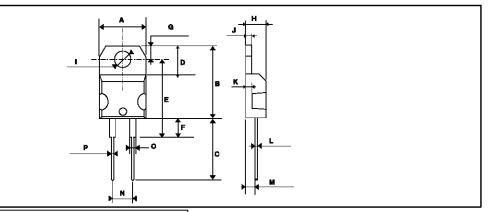
Figure 12. Turn-off switching characteristics (with series inductance)





# PACKAGE MECHANICAL DATA :

TO220AC Plastic



	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
Α	10.0	10.4	0.393	0.409		
В	15.2	15.9	0.598	0.626		
С	13	14	0.511	0.551		
D	6.2	6.6•••	0.244	0.260		
E	16.4 typ.		0.645 typ.			
F	3.5	4.2	0.137	0.165		
G	2.65	2.95	0.104	0.116		
Н	4.4	4.6	0.173	0.181		
1	3.75	3.85	0.147	0.151		
J	1.23	1.32	0.048	0.051		
K	1.27 typ.		0.050 typ.			
L	0.49	0.70	0.019	0.027		
М	2.4	2.72	0.094	0.107		
N	4.95	5.15	0.194	0.203		
0	1.14	1.70	0.044	0.067		
Р	0.61	0.88	0.024	0.034		

Cooling method: by conduction (method C) Marking: type number Weight : 2.42g Recommended torque value : 80cm. N Maximum torque value : 100cm. N

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